

N-Channel Power MOSFET

40V, 54A, 11mΩ

FEATURES

- Low R_{DS(ON)} to minimize conductive losses
- Low gate charge for fast power switching
- 100% UIS and R_g tested.
- 175°C Operating Junction Temperature
- Compliant to RoHS directive 2011/65/EU and in accordance to WEEE 2002/96/EC
- Halogen-free according to IEC 61249-2-21

KEY PERFORMANCE PARAMETERS				
PARAMETER		VALUE	UNIT	
V_D	S	40	V	
R _{DS(on)} (max)	$V_{GS} = 10V$	11	mΩ	
Q_g		23	nC	



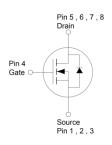




APPLICATIONS

- BLDC Motor Control
- Battery Power Management
- DC-DC converter
- Secondary Synchronous Rectification





Note: MSL 1 (Moisture Sensitivity Level) per J-STD-020

PARAMETER		SYMBOL	LIMIT	UNIT
Drain-Source Voltage		V _{DS}	40	V
Gate-Source Voltage		V_{GS}	±20	V
Continuous Drain Current (Note 1)	$T_C = 25^{\circ}C$		54	
	$T_A = 25^{\circ}C$	I _D	12	A
Pulsed Drain Current		I _{DM}	216	А
Single Pulse Avalanche Current (Note 2)		I _{AS}	17	А
Single Pulse Avalanche Energy (Note 2)		E _{AS}	43	mJ
Total Davier Dissination	$T_C = 25^{\circ}C$	D	68	10/
Total Power Dissipation	T _C = 125°C	P _D	23	W
Tetal Davis Disain ation	T _A = 25°C	Б	3.1	10/
Total Power Dissipation	T _A = 125°C	P _D	1	W
Operating Junction and Storage Temperature Range		T _J , T _{STG}	- 55 to +175	°C

THERMAL PERFORMANCE					
PARAMETER	SYMBOL	LIMIT	UNIT		
Junction to Case Thermal Resistance	R _{eJC}	2.2	°C/W		
Junction to Ambient Thermal Resistance	$R_{\Theta JA}$	48	°C/W		

Thermal Performance Note: $R_{\Theta JA}$ is the sum of the junction-to-case and case-to-ambient thermal resistances. The case-thermal reference is defined at the solder mounting surface of the drain pins. $R_{\Theta JA}$ is guaranteed by design while $R_{\Theta CA}$ is determined by the user's board design. The $R_{\Theta JA}$ limit presented here is based on mounting on a 1 in² pad of 2 oz copper.

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ELECTRICAL SPECIFICAT	TIONS (T _A = 25°C unle	ss otherwise no	oted)			
PARAMETER	CONDITIONS	SYMBOL	MIN	TYP	MAX	UNIT
Static		<u>.</u>				
Drain-Source Breakdown Voltage	$V_{GS} = 0V, I_D = 250\mu A$	BV _{DSS}	40			V
Gate Threshold Voltage	$V_{GS} = V_{DS}, I_{D} = 250 \mu A$	V _{GS(TH)}	2	3.2	4	V
Gate-Source Leakage Current	$V_{GS} = \pm 20V, V_{DS} = 0V$	I _{GSS}			±100	nA
	$V_{GS} = 0V, V_{DS} = 40V$				1	
Drain-Source Leakage Current	$V_{GS} = 0V, V_{DS} = 40V$ $T_{J} = 125^{\circ}C$	I _{DSS}			100	μΑ
Drain-Source On-State Resistance (Note 3)	V _{GS} = 10V, I _D = 12A	R _{DS(on)}		7.7	11	mΩ
Forward Transconductance (Note 3)	$V_{DS} = 10V, I_{D} = 12A$	g fs		37		S
Dynamic (Note 4)		•				
Total Gate Charge	$V_{GS} = 10V, V_{DS} = 20V,$	Q_g		23	-	
Gate-Source Charge		Q _{gs}		7		nC
Gate-Drain Charge	I _D = 12A	Q_{gd}		6		
Input Capacitance		C _{iss}		1443		
Output Capacitance	$V_{GS} = 0V, V_{DS} = 20V$	C _{oss}		147		pF
Reverse Transfer Capacitance	f = 1.0MHz	C _{rss}		80		
Gate Resistance	f = 1.0MHz	R_{g}	0.6	1.9	3.8	Ω
Switching (Note 4)						
Turn-On Delay Time	$V_{GS} = 10V, V_{DS} = 20V,$ $I_{D} = 12A, R_{G} = 2\Omega$	t _{d(on)}		3.2		
Turn-On Rise Time		t _r		20		
Turn-Off Delay Time		t _{d(off)}		10		ns
Turn-Off Fall Time		t _f		12		
Source-Drain Diode						
Forward Voltage (Note 3)	V _{GS} = 0V, I _S = 12A	V _{SD}			1.2	V
Reverse Recovery Time	I _S = 12A ,	t _{rr}		13		ns
Reverse Recovery Charge	dl/dt = 100A/µs	Q _{rr}		7		nC

Notes:

- 1. Silicon limited current only.
- 2. L = 0.3mH, $V_{GS} = 10$ V, $V_{DD} = 25$ V, $R_G = 25\Omega$, $I_{AS} = 17$ A, Starting $T_J = 25$ °C
- 3. Pulse test: Pulse Width \leq 300µs, duty cycle \leq 2%.
- 4. Switching time is essentially independent of operating temperature.

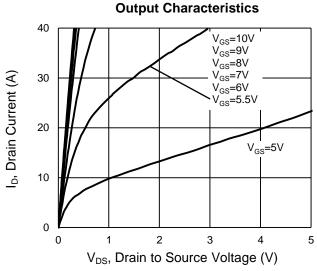
ORDERING INFORMATION

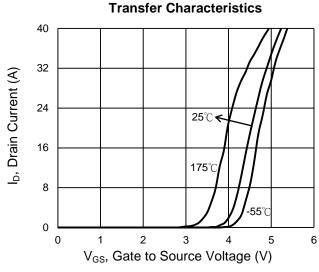
PART NO.	PACKAGE	PACKING
TSM110NB04CR RLG	PDFN56	2,500pcs / 13" Reel

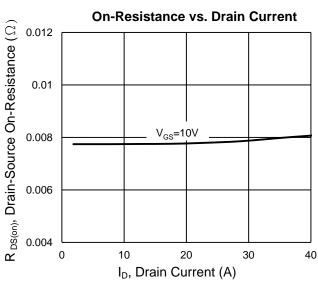


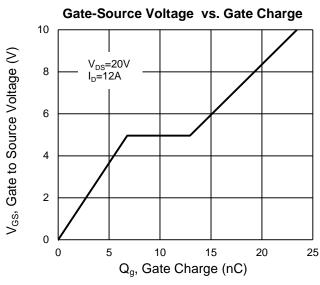
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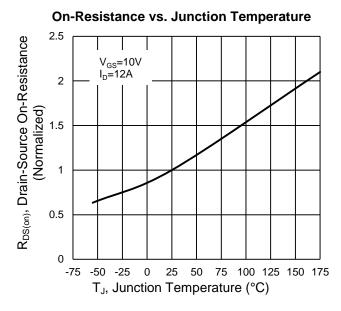
 $(T_A = 25^{\circ}C \text{ unless otherwise noted})$

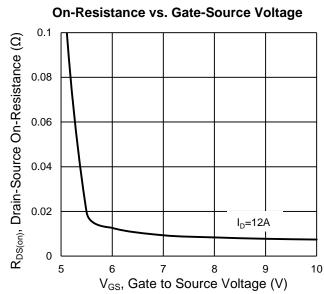












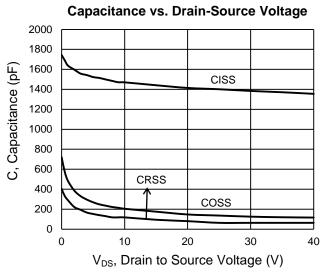
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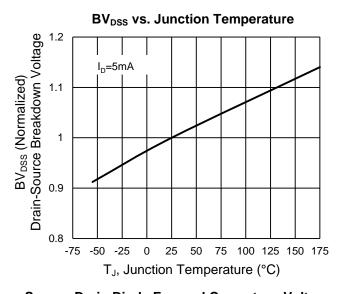
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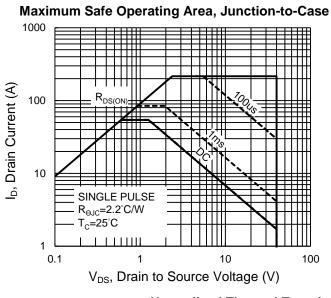


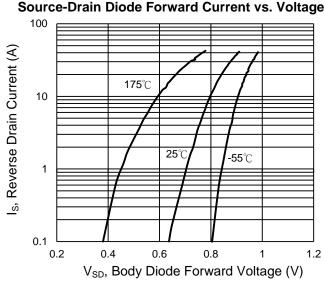
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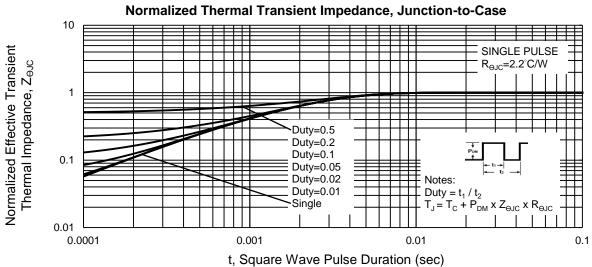
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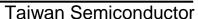






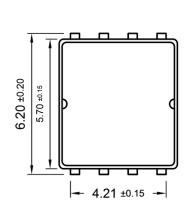


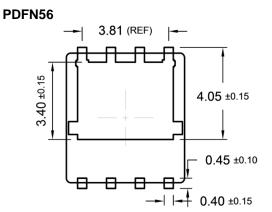
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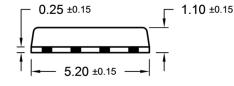


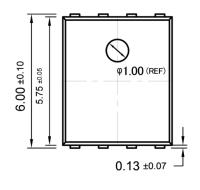


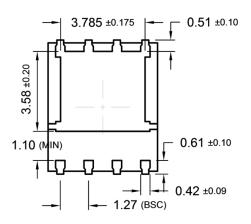
PACKAGE OUTLINE DIMENSIONS (Unit: Millimeters)

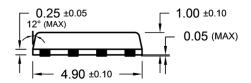




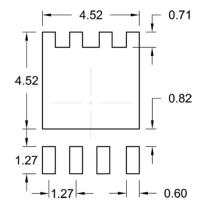




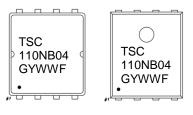




SUGGESTED PAD LAYOUT (Unit: Millimeters)



MARKING DIAGRAM



G = Halogen Free

Y = Year Code

WW = Week Code (01~52)

F = Factory Code

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